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Kind regards,

Team Nexperia

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

Rev. 03 — 31 August 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP resistor-equipped transistors

Table 1	Produ	ct overview
10010		

Type number	Package		Package		NPN/PNP	NPN/NPN
	NXP	JEITA	complement	complement		
PEMB16	SOT666	-	PEMD16	PEMH16		
PUMB16	SOT363	SC-88	PUMD16	PUMH16		

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _O	output current		-	-	-100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	



1

| | 2 3 *006aaa212*

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	

3. Ordering information

PEMB16 - plastic surface mounted package; 6 leads SO	Table 4. Ordering information				
PEMB16 - plastic surface mounted package; 6 leads SO	Type number				
		Version			
	PEMB16	SOT666			
PUMB16 SC-88 plastic surface mounted package; 6 leads SO	PUMB16	SOT363			

4. Marking

Marking code ^[1]
5G
B*7

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V _{CBO}	collector-base voltage	open emitter	-	-50	V
V _{CEO}	collector-emitter voltage	open base	-	-50	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
VI	input voltage				
	positive		-	+7	V
	negative		-	-40	V
lo	output current		-	-100	mA
I _{CM}	peak collector current		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> _	200	mW
	SOT666		[1] [2] _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device	•				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> _	300	mW
	SOT666		<u>[1] [2]</u>	300	mW

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	istor					
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> _	-	625	K/W
	SOT666		<u>[1] [2]</u>	-	625	K/W
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1] [2] _	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

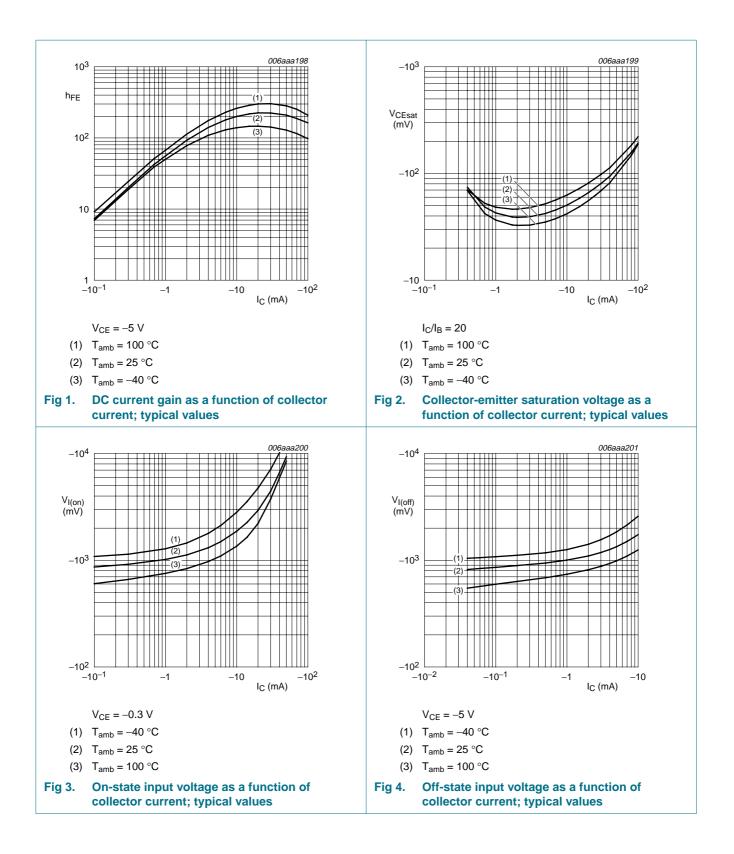
7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter	$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	-1	μA
	cut-off current	V _{CE} = -30 V; I _B = 0 A; T _j = 150 °C	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-120	μA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -5 \text{ mA}$	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10$ mA; $I_{B} = -0.5$ mA	-	-	-150	mV
V _{I(off)}	off-state input voltage	V_{CE} = -5 V; I _C = -100 μ A	-	-0.8	-0.5	V
V _{I(on)}	on-state input voltage	V_{CE} = -0.3 V; I_{C} = -2 mA	-2	-1.1	-	V
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	
C _c	collector capacitance	V _{CB} = -10 V; I _E = i _e = 0 A; f = 1 MHz	-	-	3	pF

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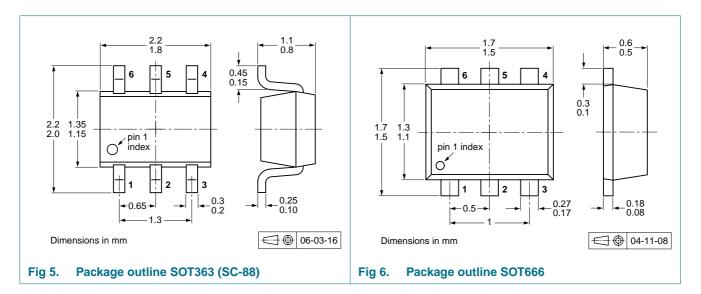
PEMB16; PUMB16

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω



PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

8. Package outline



9. Packing information

Table 9.Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.

Type number	Package	Description	Packing o	quantity	
			3000	4000	10000
PEMB16	SOT666	4 mm pitch, 8 mm tape and reel;	-	-115	-
PUMB16	SOT363	4 mm pitch, 8 mm tape and reel; T1	2 -115	-	-135
PUMB16	SOT363	4 mm pitch, 8 mm tape and reel; T2	<u>3</u> -125	-	-165

[1] For further information and the availability of packing methods, see <u>Section 12</u>.

[2] T1: normal taping

[3] T2: reverse taping

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

10. Revision history

Table 10. Revision his	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMB16_PUMB16_3	20090831	Product data sheet	-	PEMB16_PUMB16_2
Modifications: • This data sheet was changed to reflect the new company name NXP Semiconduct including new legal definitions and disclaimers. No changes were made to the tech content.				
	 Figure 5 "Pa 	ckage outline SOT363 (SC	-88)": updated	
PEMB16_PUMB16_2	20050610	Product data sheet	-	PUMB16_1
PUMB16_1	20031103	Product specification	-	-

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PEMB16_PUMB16_3
Product data sheet

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PEMB16; PUMB16

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 47 k Ω

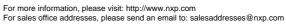
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Date of release: 31 August 2009 Document identifier: PEMB16_PUMB16_3

